



Exceptional service in the national interest



# Sandia's Quantum Photonics Research Foundry

Dr. Michael Gehl, Senior Member of Technical Staff  
National Security Photonic Center

Sandia National Laboratories is a multimission laboratory managed and operated by National Technology and Engineering Solutions of Sandia LLC, a wholly owned subsidiary of Honeywell International Inc. for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA0003525.  
SAND

## Quantum Facilities & Capabilities

### Built on significant investments over 15 years

- Over **70 projects (>\$135M)** funded by **Laboratory Directed Research and Development (LDRD)**
- Many projects funded by DOE & OGA (IARPA, DARPA, NIH, LPS,...). Over \$100M to date.
- >150 staff involved in quantum at Sandia

### Unique, hard-to-replicate capabilities

- Producing quantum devices in **multiple qubit technologies**
- Deep understanding of how device **architecture** impacts quantum applications and algorithms
- Facilities: **MESA fab, Center for Integrated Nanotechnologies (CINT), Ion Beam Lab (implantation), High Performance Computing**

### Trusted advisor to multiple government agencies

- Key agency rotations and workshop leadership

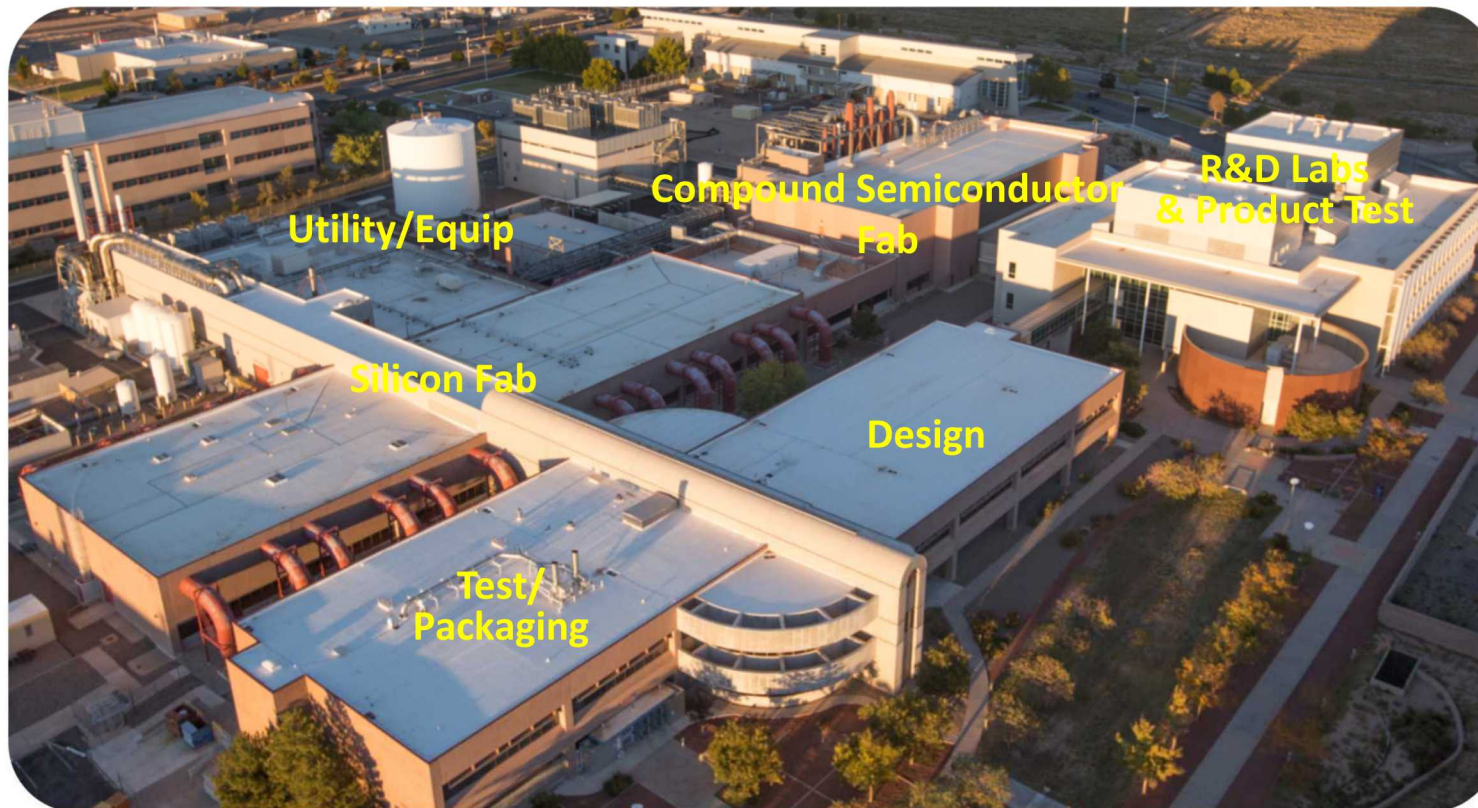




## Quantum Facilities & Capabilities

### Microsystems Engineering, Science and Applications

- Co-located research & production
- Currently dozens of products: ASICs, III-V SSICs, MEMS, FPAs, RFICs, Optoelectronics
- 400,000 Square Foot Complex, >650 Employees
- Co-located CMOS Foundry and Compound Semiconductor Fabrication



MESA



CINT



IBL



## Center for Integrated Nano-Technology (CINT)

Quantum – Dr. Michael Lilly, [mplilly@sandia.gov](mailto:mplilly@sandia.gov)

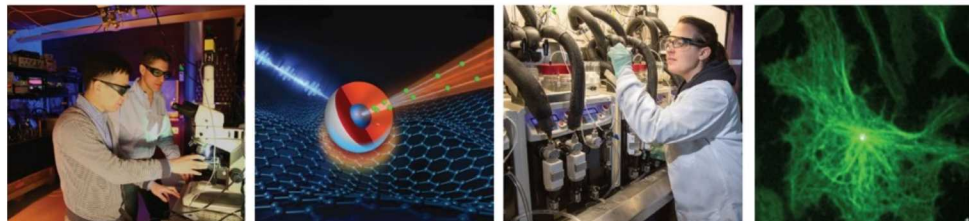
Photonics – Dr. Igal Brener, [ibrener@sandia.gov](mailto:ibrener@sandia.gov)

### Research areas:

- **In-Situ Characterization & Nanomechanics** – Developing and implementing world-leading capabilities to study the dynamic response of materials and nanosystems to mechanical, electrical, or other stimuli.
- **Nanophotonics & Optical Nanomaterials** – Synthesis, excitation, and energy transformations of optically active nanomaterials and collective or emergent electromagnetic phenomena (plasmonics, metamaterials, photonic lattices).
- **Soft, Biological & Composite Nanomaterials** – Synthesis, assembly, and characterization of soft, biomolecular, and composite nanomaterials that display emergent functionality.
- **Quantum Materials Systems** – Understanding and controlling quantum effects of nanoscale materials and their integration into systems spanning multiple length scales.



<https://cint.lanl.gov>  
<https://cint.sandia.gov>  
[cint@lanl.gov](mailto:cint@lanl.gov)



MESA



CINT

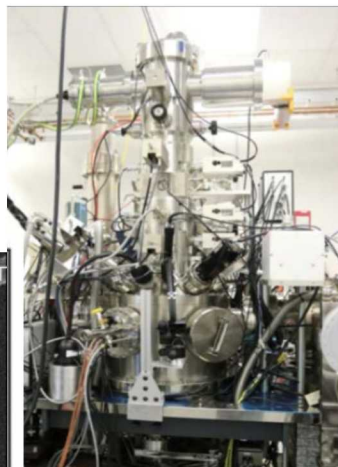
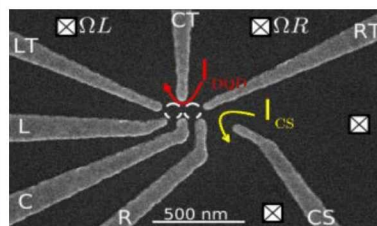
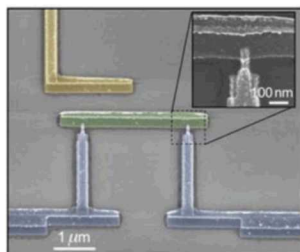


IBL

## Center for Integrated Nano-Technology (CINT)

### Quantum Information Science

- Quantum Transport and qubits
- Quantum Sensing
- Focused ion implantation



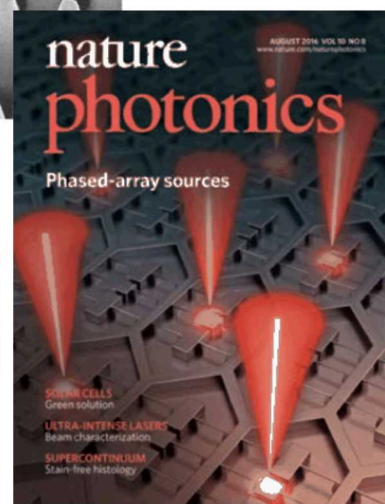
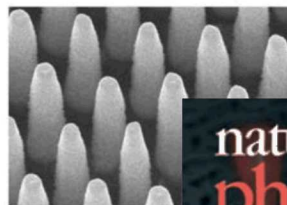
### Theory for Correlated Systems

- Techniques for strongly correlated models
- Many-body approaches
- Mean-field modeling for quantum materials



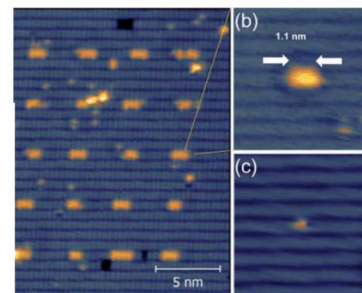
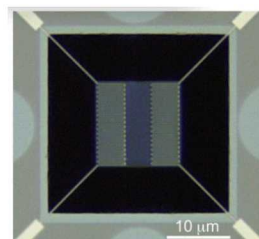
### Materials synthesis

- Ultra-High Mobility MBE
- Complex Oxide PLD
- CVD Nanowire Growth



### Forefront Lithography

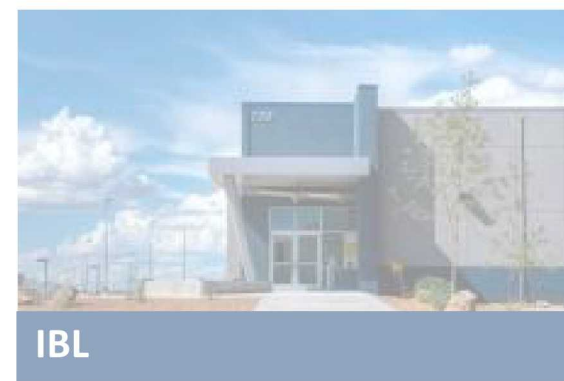
- Atomic-Precision Lithography
- Nanoscale devices



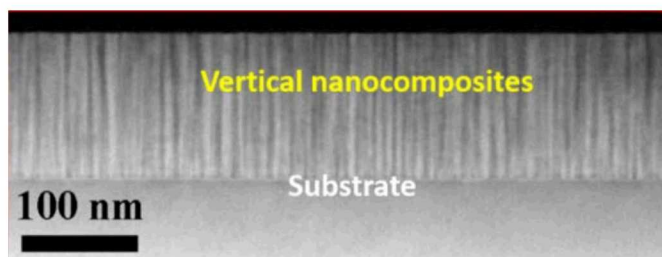
MESA



CINT



IBL

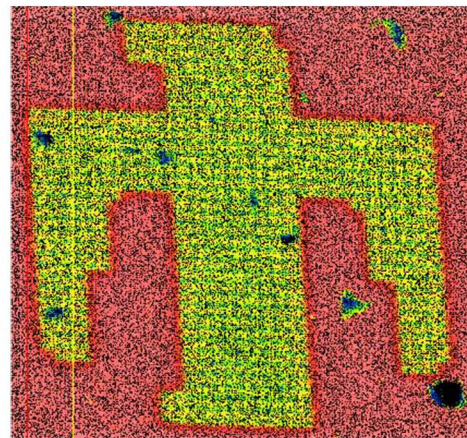




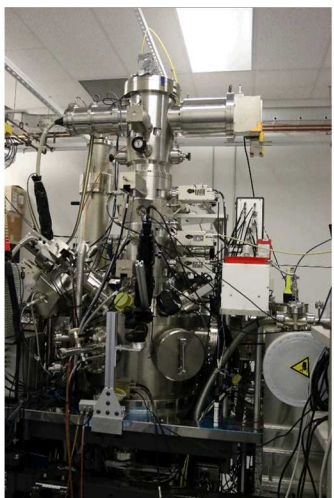
## Ion Beam Laboratory (IBL)

Dr. Edward Bielejec, [esbiele@sandia.gov](mailto:esbiele@sandia.gov)

- 6 Operational micro/nano implant systems
  - Spot sizes from 0.5nm to mm's
  - Energies from 5keV to 70MeV
  - Single ion implantation
  - <40nm targeting resolution possible
- 26 ion species in use, 40+ ions possible



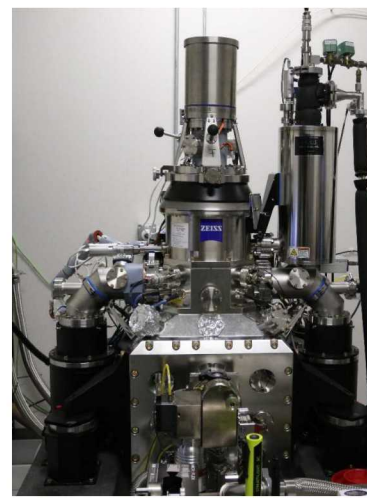
Ion Beam Induced Charging on  
PIN Diode



100 keV A&D FIB100NI



35 keV Raith Velion



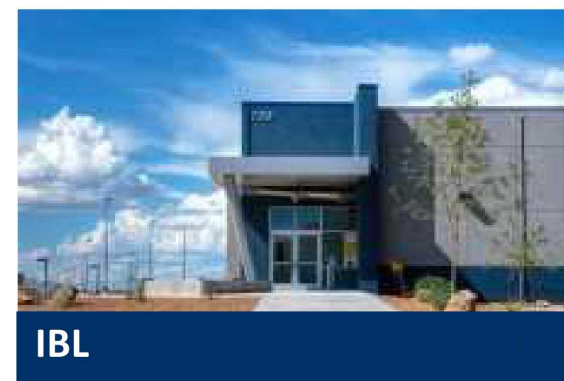
100 keV Zeiss Orion Plus



MESA



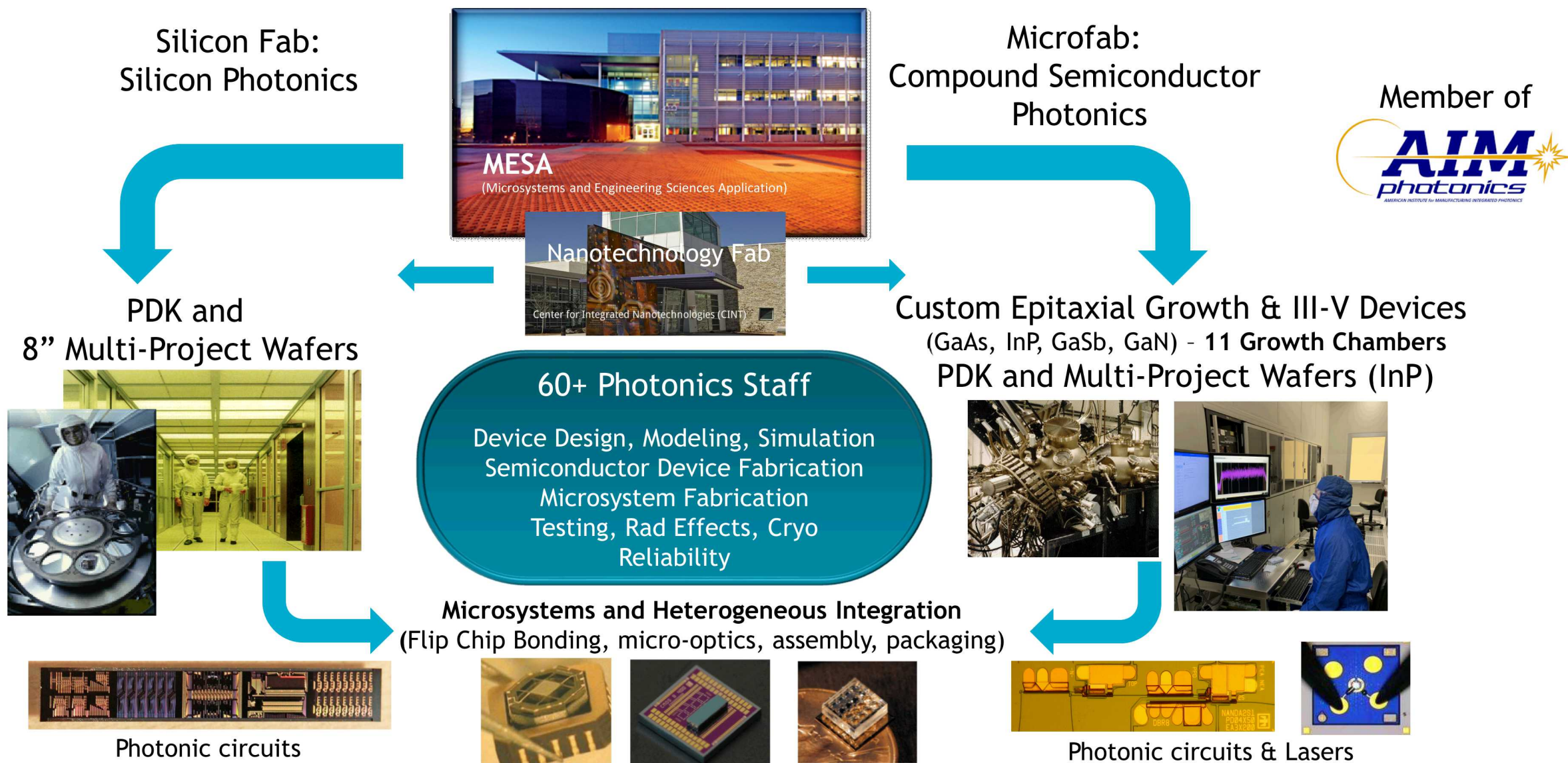
CINT



IBL



# Sandia's National Security Photonic Center





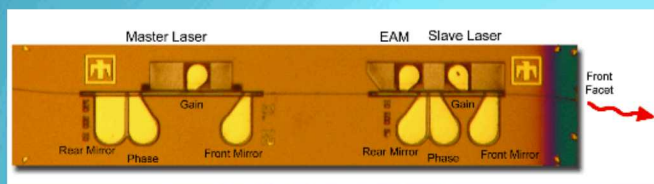
## InP Photonics

### 3 tier offerings at 1550nm

- Tier 1: one regrowth
- Tier 2: 2 regrowths (High  $P_{sat}$  Amplifier)
- Tier 3: Full custom process



RF-Optical Channelizing Filter  
1-20 GHz RF on C-Band Light

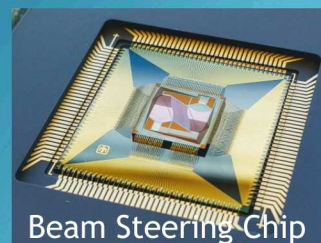


On-Chip Injection Locking  
Enhanced Modulation > 50 GHz, C-Band

## Silicon Photonics

### MPW Device Library

- 20 Active, 22 Passive Components
- Synopsis OptoDesigner
- 200mm SOI Platform
- Three Deliverables
  - Passive
  - Passive + Active
  - Passive + Active + Germanium



Beam Steering Chip

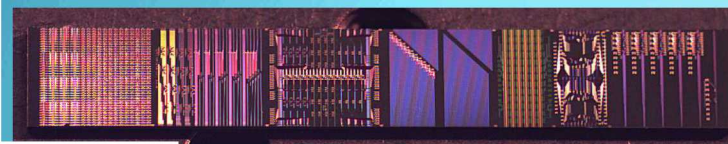
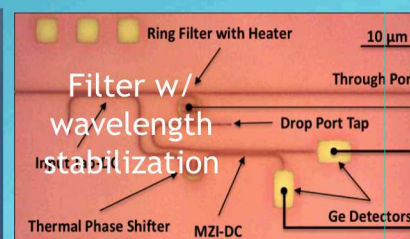


Image of MPW run, supporting Columbia, U of AZ, UC Berkeley, UCSD & Caltech

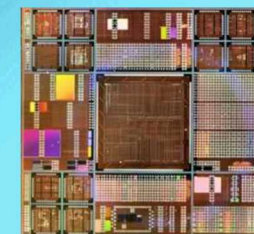
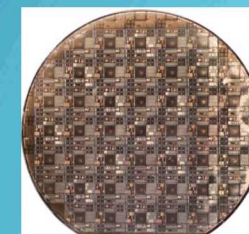
## CMOS7

### Multiple Engagement Models

- Full design & implementation by customer
- Full design & implementation by Sandia
- Anywhere in between

### Non-Standard, custom processes

- AlN for resonators
- Large-area graphene deposition
- Deep trench capacitors
- Prototype non-volatile memory
- Thick metal
- RF devices



### MPW & CMOS Design Contact:

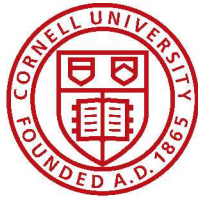
Ann Petersen, Manager  
Advanced CMOS Products/Design  
505-844-3160  
[annpete@sandia.gov](mailto:annpete@sandia.gov)

For more information:  
[photonics@sandia.gov](mailto:photonics@sandia.gov)

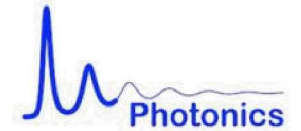


# Photonics Collaborators & Sponsors

## University



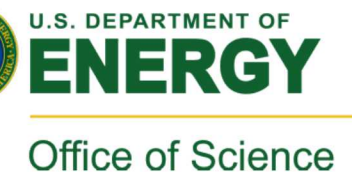
## Small Business



## Large Business



## Government



# MESA Capabilities – Silicon Photonics Platform

Dr. Anthony Lentine, [allenti@sandia.gov](mailto:allenti@sandia.gov)

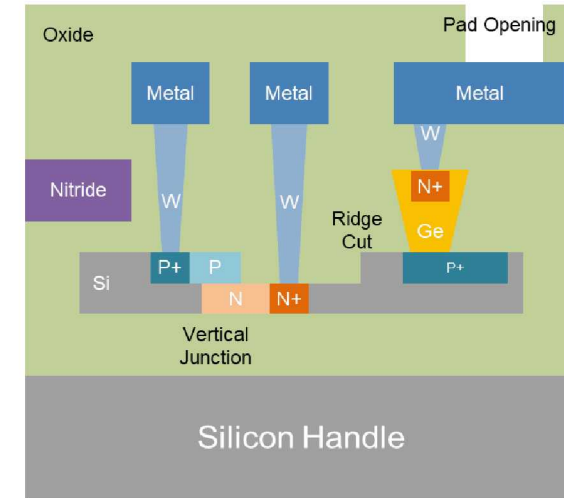
Dr. Michael Gehl, [mgehl@sandia.gov](mailto:mgehl@sandia.gov)

Mature silicon photonics capability developed through 12 years of investment

- Low power, high bandwidth modulation & detection
- Low loss optical waveguides (<0.1 dB/cm @ 1550nm)
- 200mm SOI CMOS process
- Silicon, Silicon Nitride & Alumina Waveguides
- Selective area germanium epitaxy
- Cryogenic (<1K) optimized devices

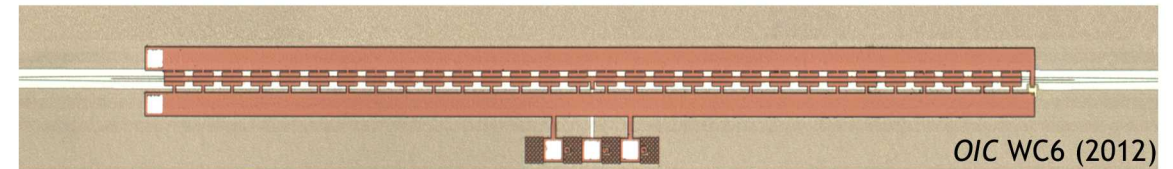
## Applications in Quantum

- Quantum Networking/Communication
- Linear Optical Quantum Computing
- Laser Source Generation & Control
- Classical Control & Data Communication



Cross section of Sandia's standard silicon photonics process

20+ GHz Electro-Optic Modulator



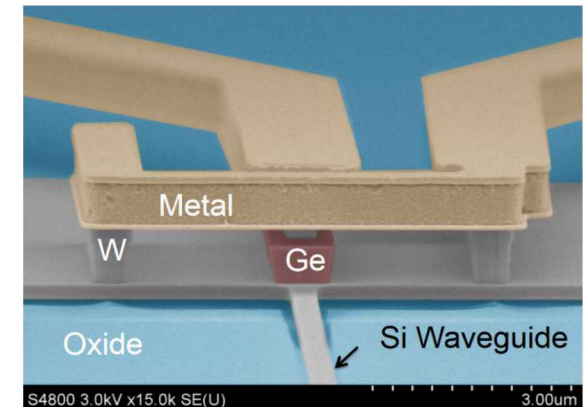
OIC WC6 (2012)

10 Gb/s Cryogenic Optical Modulator



Optica 4, 374 (2017)

Ge Single Photon Detector



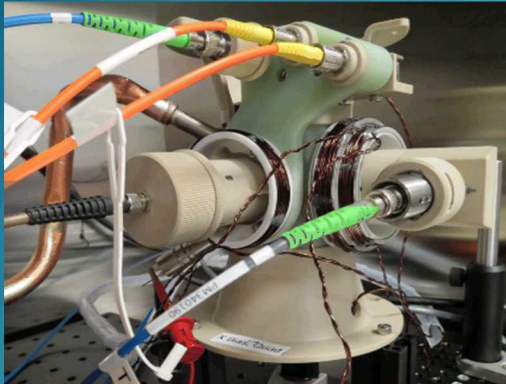
Optics express 25, 16130 (2017)



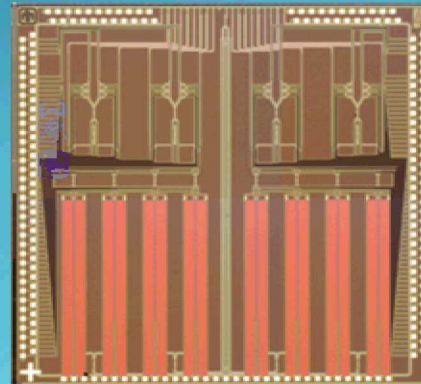
## SIGMA - Accelerometer

Strategic Inertial Guidance with MAtterwaves

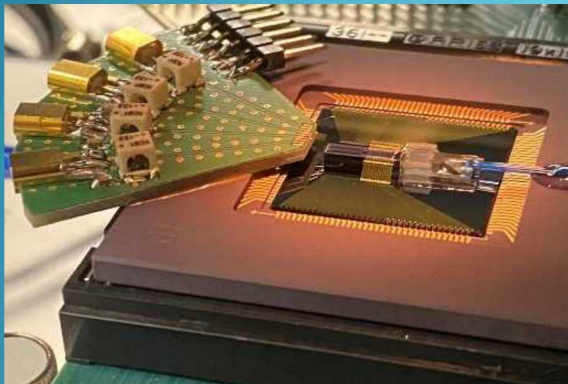
Alignment-free AI Sensor Head



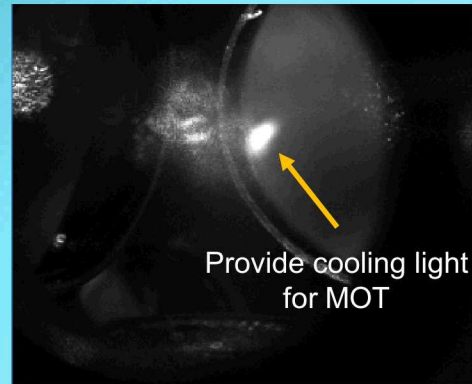
4-Channel SiP Frequency Shifter



Packaged SiP Frequency Shifter

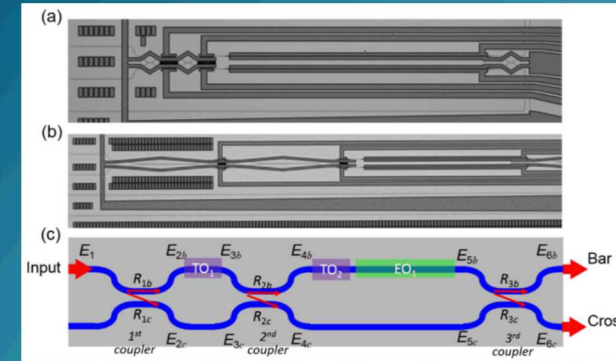


MOT Generated using SiP



Dr. Peter Schwindt, [pschwin@sandia.gov](mailto:pschwin@sandia.gov)

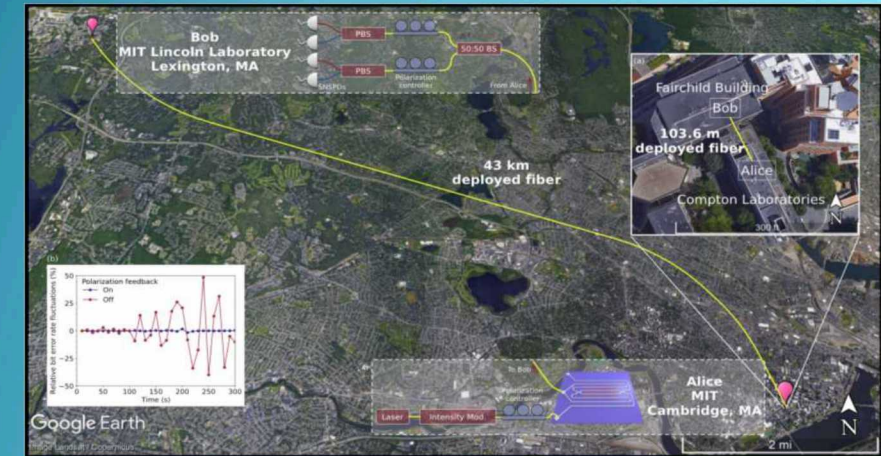
## Quantum Key Distribution



High-speed (10GHz) high-extinction ratio (>65dB)  
silicon amplitude modulator for CV QKD & Q-Sensing



T-QUAKE  
(Transceiver for  
Quantum Keys and  
Encryption)



High-speed polarization-based DV QKD  
field tests (BB84) demonstrated

Dr. Paul Davids, [pdavids@sandia.gov](mailto:pdavids@sandia.gov)



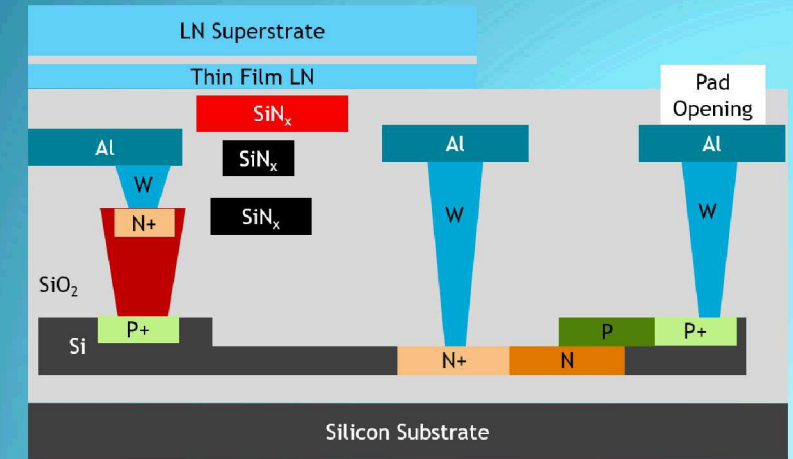
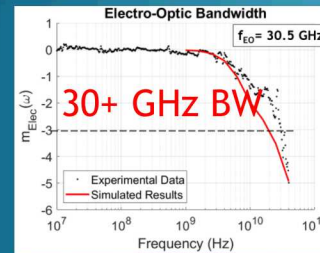
# MESA Capabilities – Heterogeneous Integration

Dr. Anthony Lentine, [allenti@sandia.gov](mailto:allenti@sandia.gov)

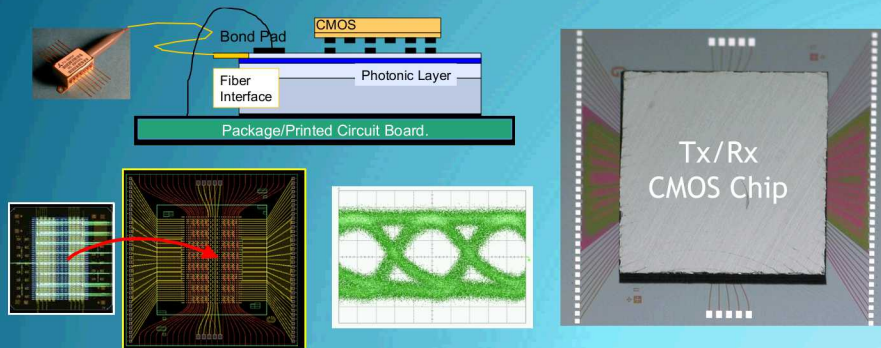
Heterogeneous integration enables miniaturization with independent material and device optimization

- Integration of  $\text{LiNbO}_3$  and III-V Lasers on Silicon Photonics
- Integration of CMOS with InGaAsP/InP, InGa/GaAs, Silicon Photonics, and other materials

## Thin Film Lithium Niobate on Si

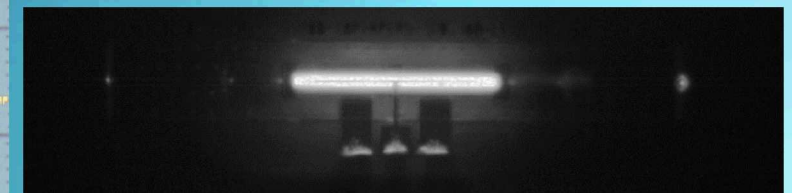
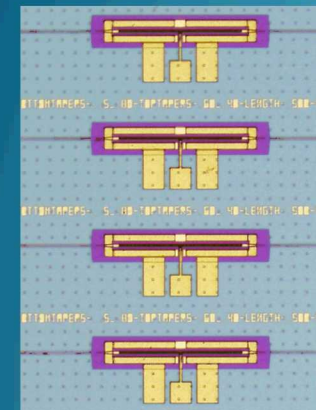


## CMOS & III-V or Si PICs



- silicon photonics on high-speed silicon ASIC
- independent optimization of electronics & photonics

## III-V Lasers & Amplifiers on Si





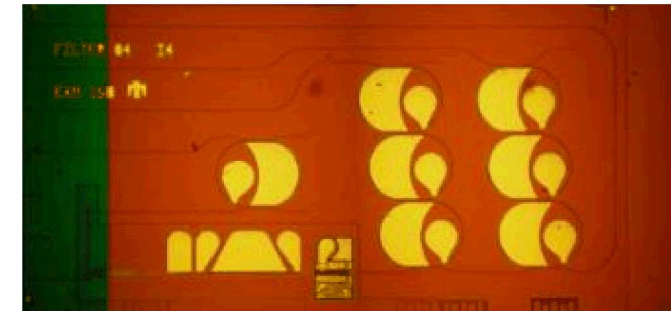
# MESA Capabilities – III/V Photonics Platform

Dr. Erik Skogen, [ejskoge@sandia.gov](mailto:ejskoge@sandia.gov)

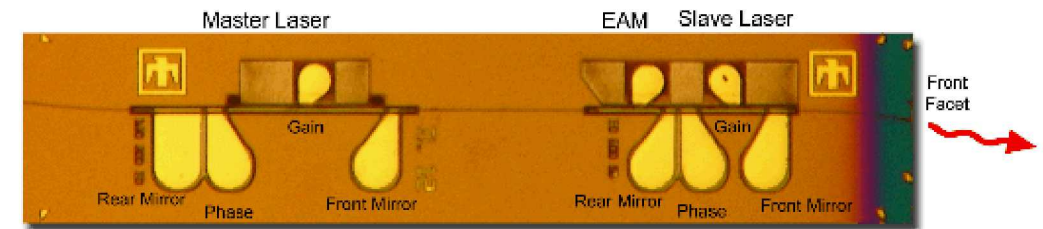
## InP-based Photonic Integrated Circuits

- Multiple band-edges by quantum-well-intermixing and/or regrowth
- Single and/or multiple epitaxial regrowth(s)
- Top-side n-type and p-type contacts
- Ridge, buried, and/or deep etch waveguide architectures

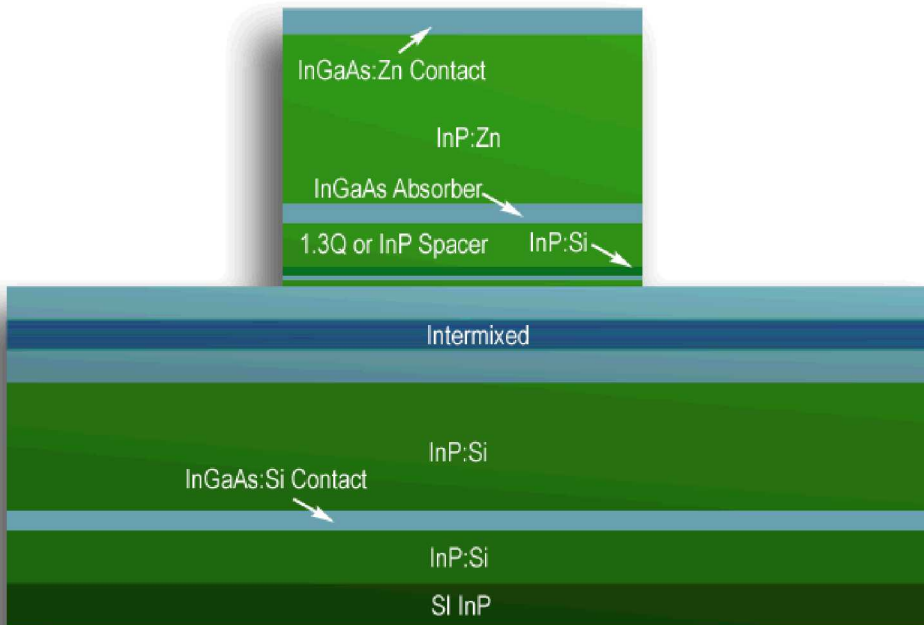
778nm lasers and modulators have been demonstrated



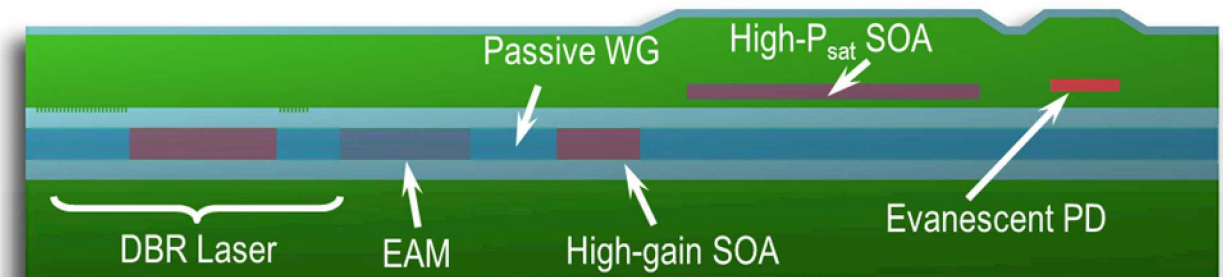
RF-Optical Channelizing Filter  
1-20 GHz RF on C-Band Light



On-Chip Injection Locking  
Enhanced Modulation > 50 GHz, C-Band



Device Cross-section (Lateral)



Device Cross-section (Longitudinal)

# MESA Capabilities – Nano-Opto-Mechanics (NOMS) & Piezo-Electrics

Dr. Matt Eichenfield, [meichen@sandia.gov](mailto:meichen@sandia.gov)

Dr. Nils Otterstrom, [ntotter@sandia.gov](mailto:ntotter@sandia.gov)

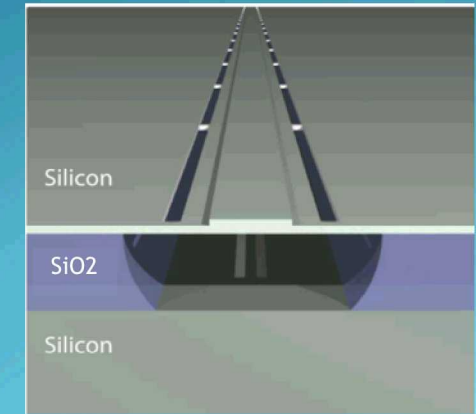
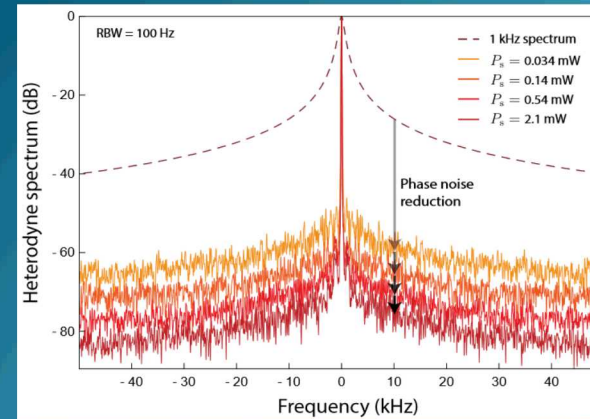
Leveraging MEMS expertise to generate new classes of optical devices

- Narrow linewidth filters
- Brillouin amplification & lasing
- Optical isolators
- On-chip delay
- Frequency Shifting
- Modulation & phase shifting

On-going quantum research

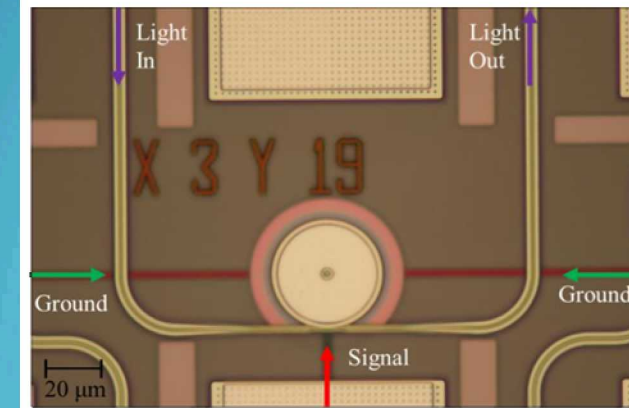
- Squeezed states
- Qubit transduction
- Opto-mechanical cooling

## Injection locked Brillouin laser in silicon



N. T. Otterstrom, arXiv:2001.04871 [physics.optics] N. T. Otterstrom, *Optica* 6, 1117 (2019)

## Piezo-optomechanically tunable modulator



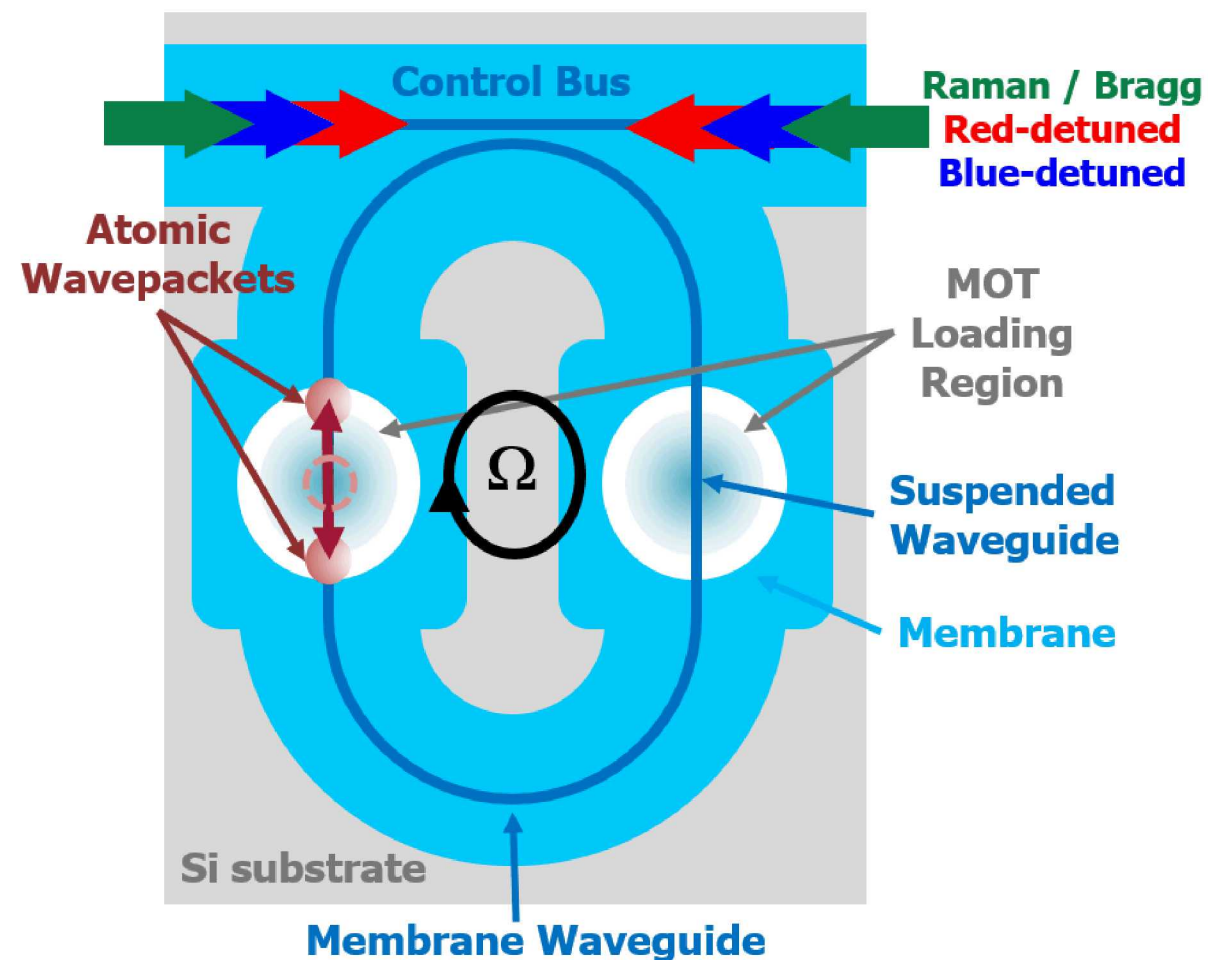
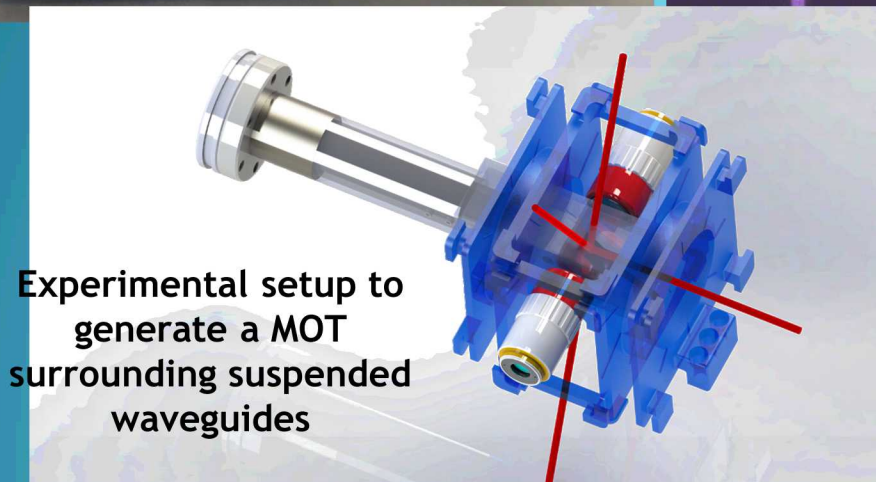
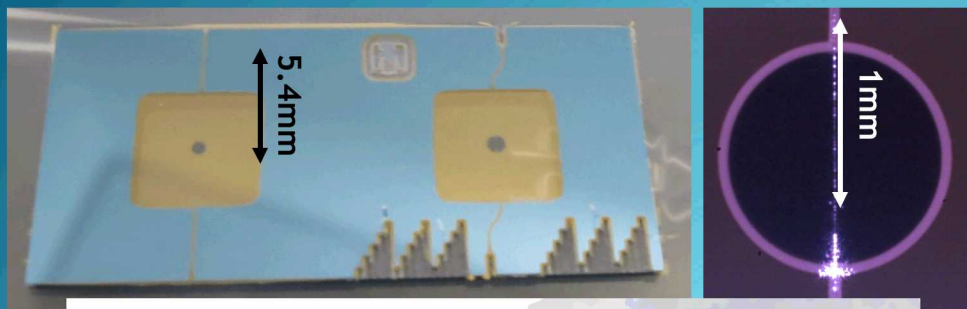
M. Eichenfield, *Optics Express* 27, 28588 (2019)



# Matterwave Sagnac Interferometer

Dr. Jongmin Lee (PI) [jlee7@sandia.gov](mailto:jlee7@sandia.gov), Dr. Michael Gehl

## Fully Suspended Membrane Waveguides

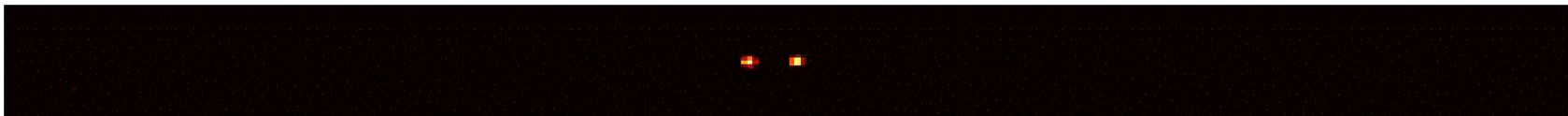


# MESA Capabilities – Ion Trapping Platform

Dr. Daniel Stick, [dlstick@sandia.gov](mailto:dlstick@sandia.gov)

- Fabricating traps for quantum computing since 2005
  - Delivered fully functioning, packaged ion traps to >12 collaborations
  - Integration capabilities include: high optical access, up to 6 metal levels, low loss UV/Vis optical waveguides, high performance SPADs, through-trap loading holes/slots, ion shuttling junctions.
- Sandia has demonstrated:
  - Calcium and Ytterbium ion trapping with high fidelity 1- and 2- qubit gate operations
  - Room temperature and cryogenic operation
  - Custom RF and electronic control system for qubit manipulation
  - Custom optical systems for individual addressing and detection of ions in linear chains
  - Low-induced-heating ion shuttling

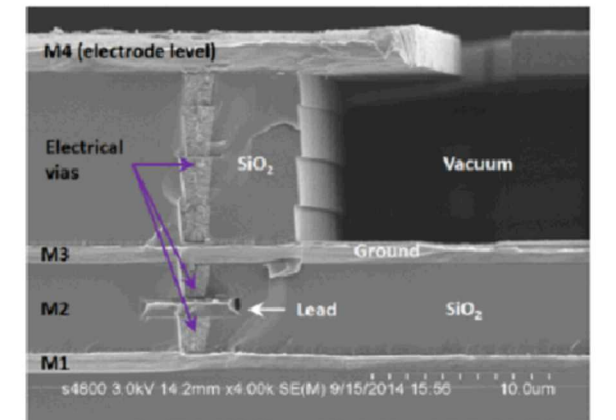
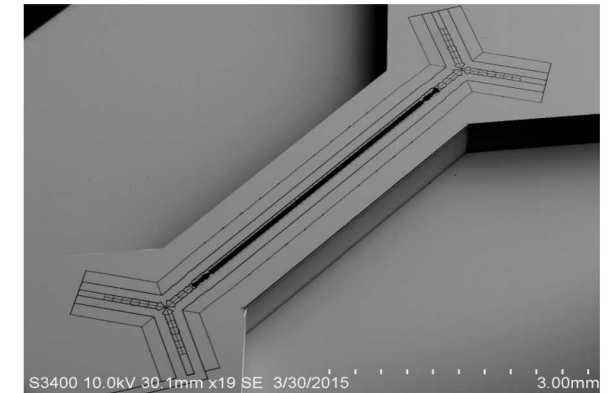
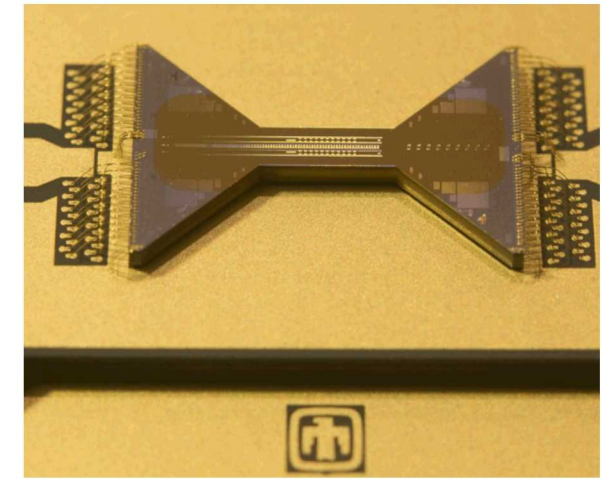
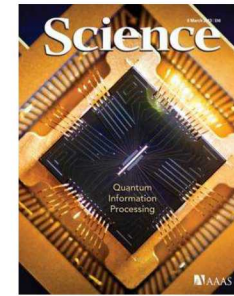
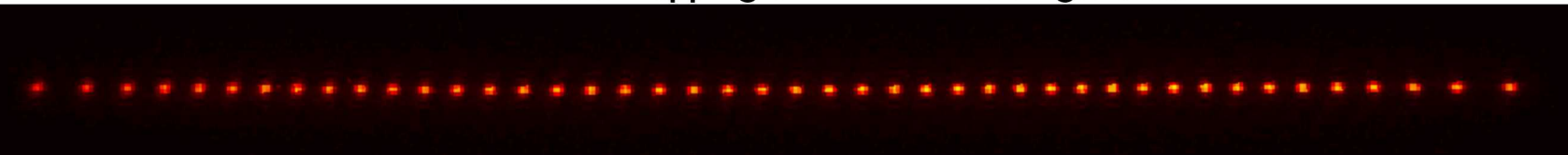
## Ion Split/Merge Control Solutions



Demonstration of Sophisticated Ion Control in a Linear Trap



Simultaneous Trapping of 44 Ions in a Single Well



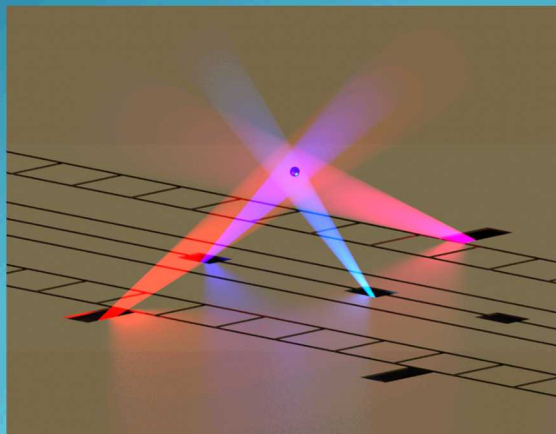
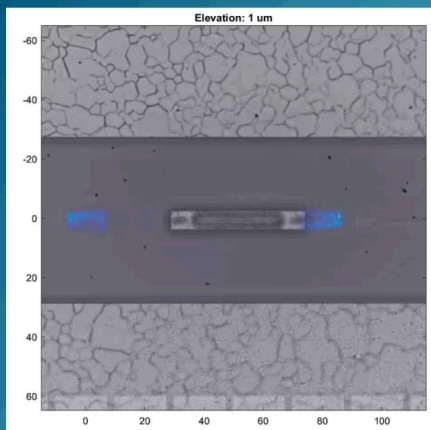


# TICTOC

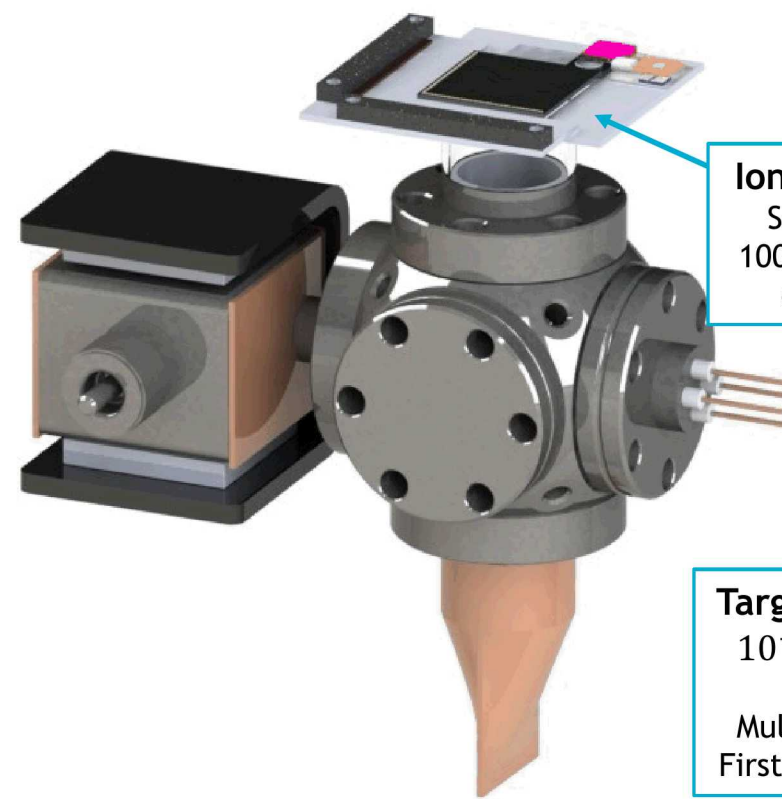
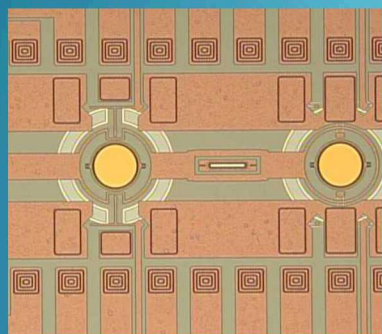
Trapped Ion Clock using photonic Technology On Chip

Dr. L. Paul Parazzoli (PI) [lpparaz@sandia.gov](mailto:lpparaz@sandia.gov), Dr. Hayden McGuinness, Dr. Michael Gehl

Ionization Beams Converging Multi-Wavelength Integrated Photonics



Integrated Single Photon Detectors Low loss waveguides & gratings



**Ion Trap/PIC Interposer**  
Solder Attached to UHV  
100+ electrical & optical IO  
delivered through PIC

**Target Demonstrations**  
 $10^{-14}/\sqrt{\tau}$  for 100,000 s  
<1/2 liter volume  
Multi-ensemble protocol  
First surface ion trap clock

# MESA Capabilities – QSCOUT

Quantum Scientific Computing Open User Testbed

Dr. Susan Clark, [sclark@sandia.gov](mailto:sclark@sandia.gov), [qscout@sandia.gov](mailto:qscout@sandia.gov)

## Goals

- Quantum processor for Scientific applications
- High fidelity operations
- Full connectivity between qubits
- Open system, fully specified operations and hardware
- Quantum assembly language enabling low-level access for control down to gate pulses
- Open for vertical integration by users

## Realization

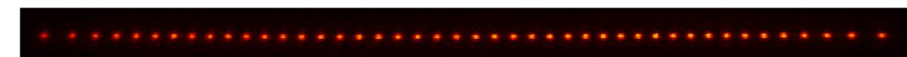
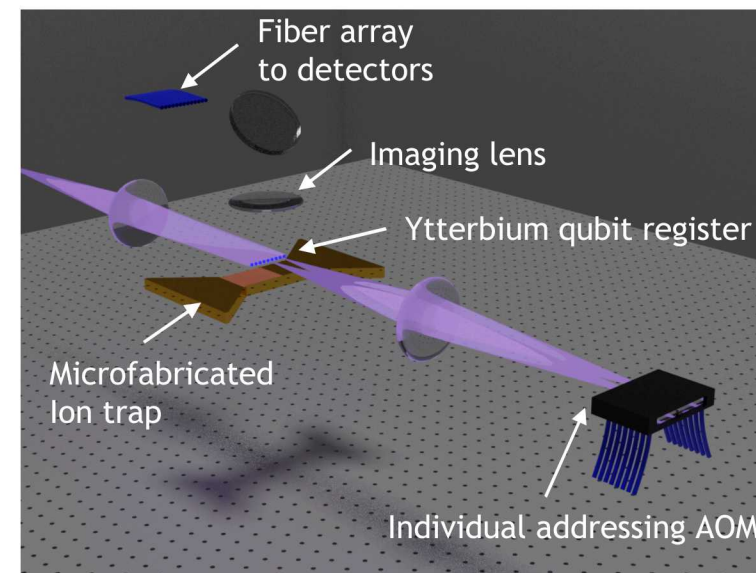
- Trapped ion system using chain of ytterbium-171 ions:
  - Near-ideal prep and measure, no idle errors, lowest gate errors
- Reconfigurable in software
- All-to-all Connectivity

## User Access

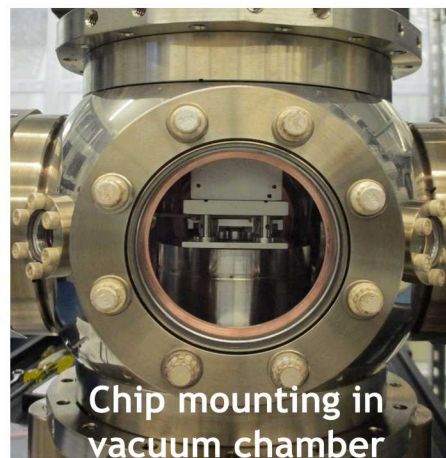
- In collaboration with SNL QSCOUT scientists
- First round of users includes operations with 3 qubits
- Expected start November 2020
- Calls for user proposals: <https://qscout.sandia.gov>

## Current Status

- System design complete
- Realized high-fidelity single-qubit operations
- Qubit Coherence times > 13s



Chain of trapped ions



Gate	Entanglement Infidelity	1/2 Trace Distance	1/2 Diamond-Dist	Eigenvalue Ent. Infidelity	Eigenvalue 1/2 Diamond-Dist
Gi	0.00019	0.000817	--	0.00019	0.001081
Gx	0.00004	0.001003	--	0.000039	0.000073
Gy	0.000001	0.001151	--	$3 \times 10^{-7}$	0.000876

Measured QSCOUT gate infidelities



# Conclusion

15+ years of significant investments resulting in world-class quantum expertise and quantum enabling technologies

- Ion traps
- Neutral atoms
- Donors in silicon
- Diamond vacancies
- Silicon & III/V photonics spanning UV to SWIR

Large number of existing collaborative quantum research projects

- QSCOUT – User testbed
- TICTOC – Compact ion trap clock
- Photonic/CMOS multi-project wafers

Developing a quantum workforce through graduate students, post-docs and early career staff

- 60+ photonic staff, 150+ quantum staff

